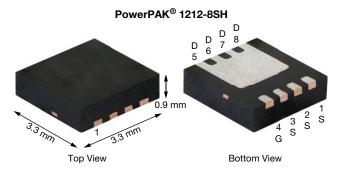
# SiSH108DN

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**Vishay Siliconix** 

COMPLIANT

# N-Channel 20 V (D-S) Fast Switching MOSFET



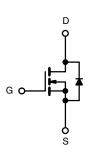
PRODUCT SUMMARY	
V <sub>DS</sub> (V)	20
$R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS}$ = 10 V	0.0049
$R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS}$ = 4.5 V	0.0061
Q <sub>g</sub> typ. (nC)	20
I <sub>D</sub> (A)	22
Configuration	Single

### **FEATURES**

- TrenchFET<sup>®</sup> Gen II power MOSFET for ultra low on-resistance RoHS
- 100 % R<sub>q</sub> tested
- HALOGEN Material categorization: for definitions of **FREE** compliance please see www.vishay.com/doc?99912

#### **APPLICATIONS**

- Synchronous rectification
- · Point-of-load converters
- Protection devices
- Hot swap



N-Channel MOSFET

ORDERING INFORMATION	
Package	PowerPAK 1212-8
Lead (Pb)-free and halogen-free	SiSH108DN-T1-GE3

<b>ABSOLUTE MAXIMUM RATINGS</b>	(T <sub>A</sub> = 25 °C, un	less otherwise	noted)			
PARAMETER		SYMBOL	10 s	STEADY STATE	UNIT	
Drain-source voltage		V <sub>DS</sub>	20	20		
Gate-source voltage		V <sub>GS</sub>	± 16	± 16	V	
Continuous drain current (T <sub>J</sub> = 150 °C) <sup>a</sup>	T <sub>A</sub> = 25 °C	- I <sub>D</sub>	22	14		
	T <sub>A</sub> = 70 °C		17.6	11.2		
Pulsed drain current			60	60	A	
Continuous source current (diode conduction) <sup>a</sup>		I <sub>S</sub>	3.2	1.3		
Single avalanche current	L = 0.1 mH	I <sub>AS</sub>	22	22		
Single avalanche energy		E <sub>AS</sub>	24	24	mJ	
Maximum power dissipation <sup>a</sup>	T <sub>A</sub> = 25 °C	PD	3.8	1.5	W	
	T <sub>A</sub> = 70 °C		2.0	0.8	vv	
Operating junction and storage temperature range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +150		°C	
Soldering recommendations (peak temperature) b, c			260			

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT
Maximum junction-to-ambient <sup>a</sup>	t ≤ 10 s	R <sub>thJA</sub>	24	33	°C/W
	Steady state		65	81	
Maximum junction-to-case (drain)	Steady state	R <sub>thJC</sub>	1.9	2.4	

#### Notes

a. Surface mounted on 1" x 1" FR4 board

b. See solder profile (www.vishav.com/doc?73257). The PowerPAK 1212-8SH is a leadless package within the PowerPAK 1212-8 package family. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection

c. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components

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For technical questions, contact: pmostechsupport@vishay.com

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### SiSH108DN

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PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static			•				
Gate threshold voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = 250 \ \mu A$	1	-	2	V	
Gate body leakage	I <sub>GSS</sub>	$V_{DS} = 0 V, V_{GS} = \pm 16 V$	-	-	± 100	nA	
7		$V_{DS} = 20 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$	-	-	1		
Zero gate voltage drain current	IDSS	$V_{DS}$ = 20 V, $V_{GS}$ = 0 V, $T_J$ = 55 °C	-	-	5	μA	
On-state drain current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \ge 5 \text{ V}, \text{ V}_{GS} = 10 \text{ V}$	40	-	-	А	
	Р	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 22 \text{ A}$	-	0.0041	0.0049		
Drain-source on-state resistance <sup>a</sup>	R <sub>DS(on)</sub>	$V_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 19.7 \text{ A}$	-	0.0050	0.0061	Ω	
Forward transconductance a	9 <sub>fs</sub>	$V_{DS} = 15 \text{ V}, \text{ I}_{D} = 22 \text{ A}$	-	88	-	S	
Diode forward voltage <sup>a</sup>	V <sub>SD</sub>	$I_{S} = 3.2 \text{ A}, V_{GS} = 0 \text{ V}$	-	0.75	1.2	V	
Dynamic <sup>b</sup>							
Total gate charge	Qg		-	20	30		
Gate-source charge	Q <sub>gs</sub>	$V_{DS}$ = 10 V, $V_{GS}$ = 4.5 V, $I_{D}$ = 22 A	-	6.3	-	nC	
Gate-drain charge	Q <sub>gd</sub>		- 4.9		-	]	
Gate resistance	Rg	f = 1 MHz	0.7	1.4	2.1	Ω	
Turn-on delay time	t <sub>d(on)</sub>		-	10	15		
Rise time	t <sub>r</sub>	$V_{DD}$ = 20 V, $R_L$ = 20 $\Omega$	-	10	15		
Turn-off delay time	t <sub>d(off)</sub>	$I_D \cong$ 1 A, $V_{GEN}$ = 10 V, $R_g$ = 6 $\Omega$	-	60	130	ns	
Fall time	t <sub>f</sub>		-	10	15		
Source-drain reverse recovery time	t <sub>rr</sub>	I2 0 0 di/dt _ 100 0 /::::	-	30	60		
Reverse recovery charge	Q <sub>rr</sub>	I <sub>F</sub> = 3.2 A, di/dt = 100 A/μs	-	20	36	nC	

Notes

a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %

b. Guaranteed by design, not subject to production testing

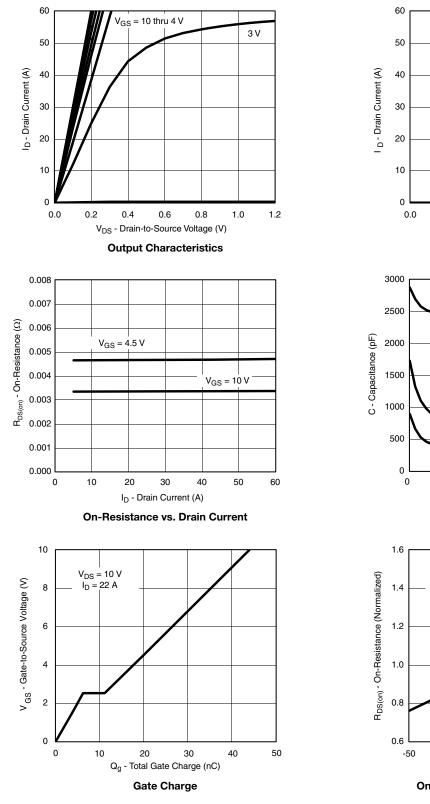
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

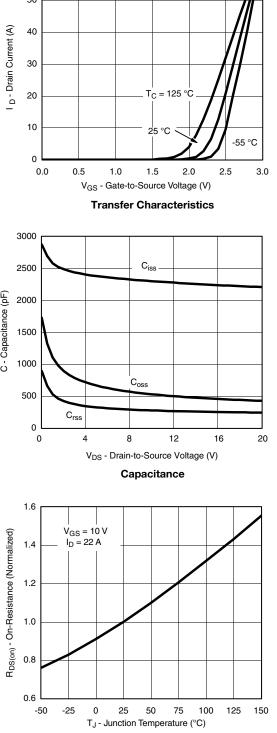
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### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)





**On-Resistance vs. Junction Temperature** 

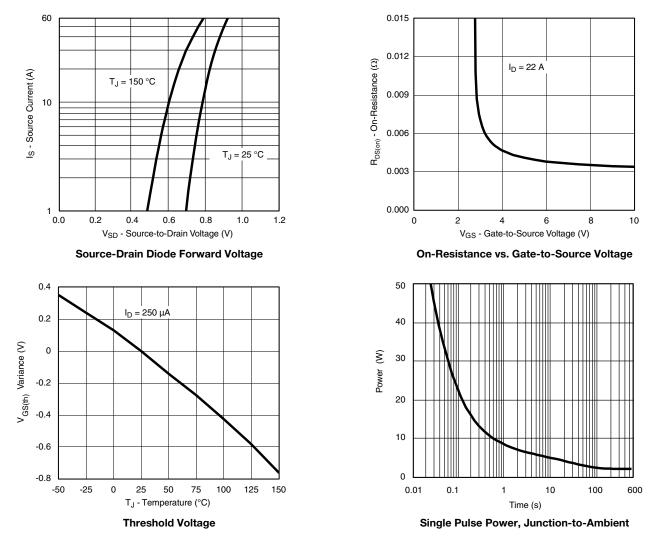
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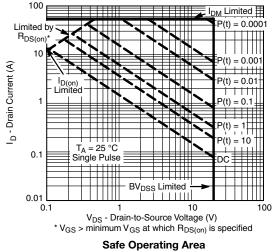


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### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)





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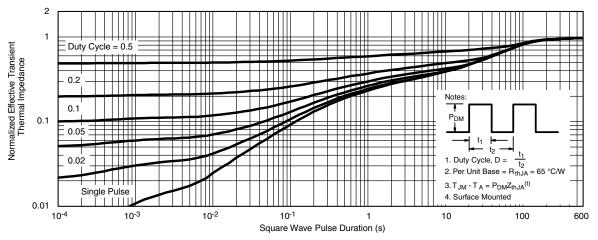
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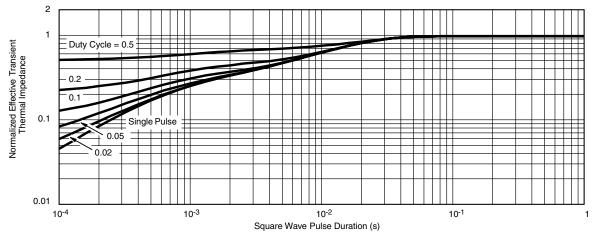


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### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

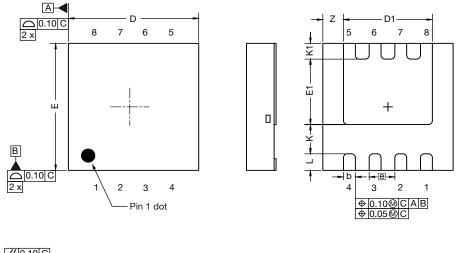
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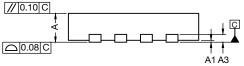
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# Case Outline for PowerPAK<sup>®</sup> 1212-SWLH and PowerPAK<sup>®</sup> 1212-8SH

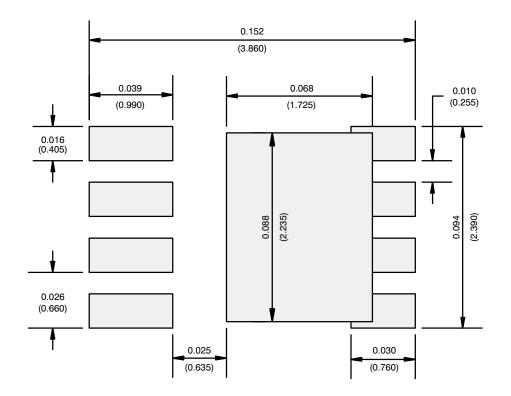




MIN.	NOM.	MAX.	
0.032	0.035	0.038	
0.000	-	0.002	
0.008 ref.			
0.010	0.012	0.014	
0.126	0.130	0.134	
0.085	0.089	0.093	
0.126	0.130	0.134	
0.063	0.067	0.071	
0.026 bsc.			
0.030 ref.			
0.016 ref.			
0.013	0.017	0.021	
0.021 ref.			
	0.013	0.013 0.017	



### **RECOMMENDED MINIMUM PADS FOR PowerPAK® 1212-8 Single**



Recommended Minimum Pads Dimensions in Inches/(mm)

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